

Docket No.: 57454-962

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Hideto HIDAKA

Serial No.: Divisional of

Appln. Serial No. 09/986,865

: Group Art Unit: Not yet assigned

Filed: July 21, 2003

: Examiner: Not yet assigned

For: THIN FILM MAGNETIC MEMORY DEVICE WITH MEMORY CELLS INCLUDING A  
TUNNEL MAGNETIC RESISTIVE ELEMENT

**INFORMATION DISCLOSURE STATEMENT**

Mail Stop Patent Application  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

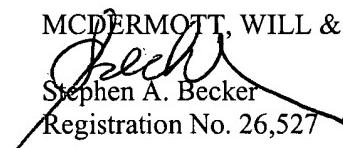
In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The references were cited by or submitted to the U.S. Patent and Trademark Office in parent application Serial No. 09/986,865, filed November 13, 2001, which is relied upon for an earlier filing date under 35 USC 120. Thus, copies of these references are not attached. 37 CFR 1.98(d).

Respectfully submitted,

MCDERMOTT, WILL & EMERY

  
Stephen A. Becker

Registration No. 26,527

600 13<sup>th</sup> Street, N.W.  
Washington, DC 20005-3096  
(202) 756-8000 SAB:blp  
Facsimile: (202) 756-8087  
**Date: July 21, 2003**

INFORMATION DISCLOSURE CITATION IN AN APPLICATION			ATTY. DOCKET NO. <b>57454-962</b>	SERIAL NO. <b>Divisional of Appln.</b> <b>Serial No. 09/986,865</b>		
			APPLICANT <b>Hideto HIDAKA</b>			
(PTO-1449)			FILING DATE <b>July 21, 2003</b>	GROUP <b>Not yet assigned</b>		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	6,046,929	04/2000	Aoki et al.			
	6,349,054	02/2002	Hidaka			
FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation
						Yes
						No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
	Scheuerlein, et al. "A 10ns Read ands Write Non-Volatile Memory Array Using A Magnetic Tunnel Junction and FET Switch in Each Cell," ISSCC Digest of Technical Papers, TA7.2, February 2000, pages 94-95, 128-129 and 409-410					
	Durlam, et al., "Nonvolatile RAM Based on Magnetic Tunnel Junction Elements ISSCC Digest of Technical Papers, TA7.3, February 2000, pages 96-97, 130-131 and 410-411					
	Naji, et al, "A 256kb 3.0V iTiMTJ Nonvolatile Magnetoresistive RAM," ISSCC Digest of Technical Papers, TA7.6, February 2001, pages 122-123 and 438					
	Co-Pending US Patent Application Serial Number 09/887,321, Filed June 25, 2001					
EXAMINER	DATE CONSIDERED					

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.